Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
Ll	0	((lower bottom) near electrode\$1) near2 on near2 ((impurity diffus\$3 dop\$3) near (region area))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 16:57
L2	202	((lower bottom) near electrode\$1) near2 ((impurity diffus\$3 dop\$3) near (region area))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 17:12
L3	36	2 and (trench with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 17:15
L4	4	("5281555" "5361234" "5410161" "5689126").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/01 17:08
L5	922	((lower bottom) near electrode\$1) with ((impurity diffus\$3 dop\$3) near (region area))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 17:14
L6	745	5 and ((upper top) near electrode\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 17:14
L7	121	6 and (trench with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/01 17:15
S1	11651	257/68,71,295-314,324-326,330-334.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 17:24
S2	4508	438/3,240,259,270,271,589.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 17:24
S3	15476	257/68,71,295-314,324-326,330-334.ccls. or 438/3,240,259,270,271,589.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 17:27

S4	1825	(257/68,71,295-314,324-326,330-334.ccls. or 438/3,240,259,270,271,589.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 18:04
S5	28	((257/68,71,295-314,324-326,330-334. ccls. or 438/3,240,259,270,271,589.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))) and (capacitor\$1 with ferroelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 18:04
S6	266	((257/68,71,295-314,324-326,330-334. ccls. or 438/3,240,259,270,271,589.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))) and ((diffus\$3 dop\$3) near5 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 18:13
S7	3	(((257/68,71,295-314,324-326,330-334. ccls. or 438/3,240,259,270,271,589.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))) and ((diffus\$3 dop\$3) near5 bottom near2 (groove\$1 trench\$2))) and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 18:14
S8	9	("5032882" "5381364" "5400275" "5447882" "5541872" "5598366" "5817552" "5874760" "5991188").PN.	USPAT	OR	ON	2004/09/14 17:57
S9	410523	"257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR .	ON	2004/09/14 18:04
S10	5565	("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 18:17
S11	44	(("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))) and (capacitor\$1 with ferroelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:49
S12	468	(("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))) and ((diffus\$3 dop\$3) near5 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:12
S13	7	((("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and (gate near2 (groove\$1 recess\$2 trench\$2))) and ((diffus\$3 dop\$3) near5 bottom near2 (groove\$1 trench\$2))) and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:08
S14	447	("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:19

S15	194	(("257"/\$.ccls. "438"/\$.ccls. "365"/\$.ccls.) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:08
S16	87090	substrate with (trench groove)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:12
S17	445	(substrate with (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:13
S18	5	((substrate with (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))) and ((gate near electrode) near2 (side near wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:20
S19	48	((substrate with (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))) and ((gate near electrode) near2 (trench groove))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:18
S20	2488	((gate near electrode) near2 (trench groove))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:18
S21	50	(((gate near electrode) near2 (trench groove))) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:21
S22	3	((gate near electrode) near2 (side near wall) near2 (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:07
S23	90	(gate near electrode) near2 (side near wall) near2 (trench groove)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:22
S24	3004	capacitor\$1 with (ferroelectric near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:51

S25	0	(capacitor\$1 with (ferroelectric near (layer film))) and ((diffus\$3 dop\$3) with (contact near2 (side near wall)) with (trench groove))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:53
S26	7	(capacitor\$1 with (ferroelectric near (layer film))) and ((diffus\$3 dop\$3) with (contact near2 (side near wall)))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 19:55
S27	66	(capacitor\$1 with (ferroelectric near (layer film))) and ((diffus\$3 dop\$3) with (trench groove))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:06
S28	48511	(side near wall) with (trench groove)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:07
S29	0	(((side near wall) with (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))) and (capacitor\$1 with (ferroelectric near (layer film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:08
S30	67	(((side near wall) with (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))) and (gate near electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/14 20:08
S31	141	((side near wall) with (trench groove)) and ((diffus\$3 dop\$3) near2 bottom near2 (groove\$1 trench\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM TDB	OR	ON	2004/09/14 20:09